Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO263 (D2PAK) plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom/Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED/OLED TV
- Motor Drives

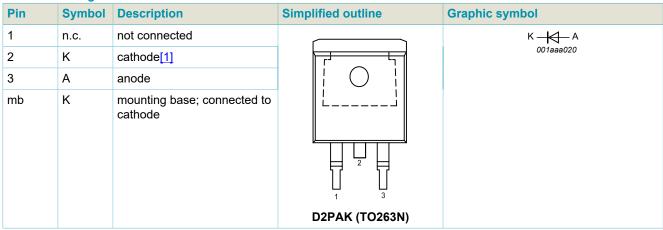
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 113 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	-	10	A
Tj	junction temperature		-	-	175	°C
Static charac	teristics					
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
Dynamic cha	racteristics					
Q _r	recovered charge	I _F = 10 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; <u>Fig. 8</u> ; <u>Fig. 9</u>	-	15	22	nC

5. Pinning information

Table 2. Pinning information



^[1] It is not possible to connect to pin 2 of the TO263 package.

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
NXPSC10650B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	TO263N		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	650	V
V_{RWM}	crest working reverse voltage		-	650	V
V_R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 113 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; square-wave pulse	-	20	А
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	50	Α
	forward current	t_p = 10 μ s; $T_{j(init)}$ = 25 °C; square-wave pulse	-	450	A
l ² t	I ² t for fusing	sine-wave pulse; T _{j(init)} = 25°C; t _p = 10 ms	-	12.5	A²s
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-	175	°C

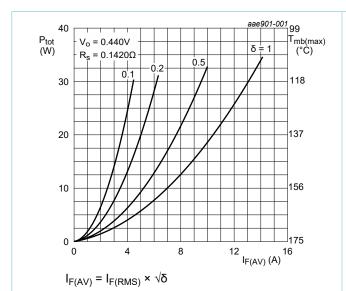


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

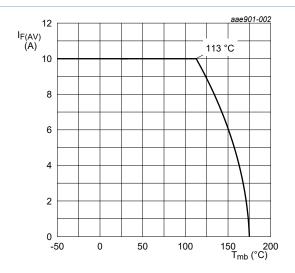


Fig. 2. Forward current as a function of mounting base temperature; maximum values

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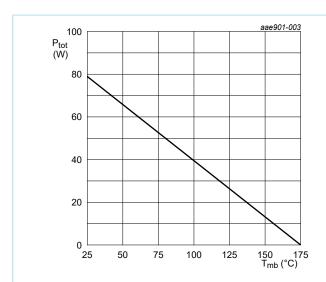


Fig. 3. Total power dissipation as a function of mounting base temperature

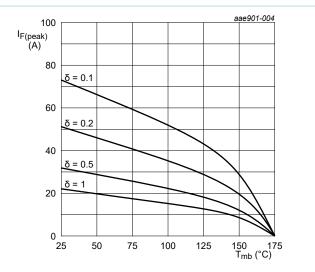


Fig. 4. Current derating as a function of mounting base temperature

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	Device mounted on an FR4 Printed- Circuit Board (PCB)	-	50	-	K/W

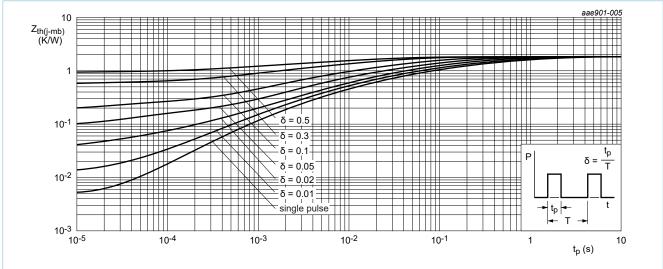
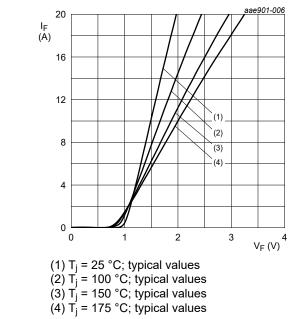


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					_
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 7</u>	-	-	250	μA
		V _R = 650 V; T _j = 150 °C; <u>Fig. 7</u>	-	-	800	μΑ
		$V_R = 600 \text{ V}; T_j = 25 \text{ °C}; Fig. 7$	-	-	100	μA
		V _R = 600 V; T _j = 150 °C; <u>Fig. 7</u>	-	-	450	μΑ
Dynamic ch	naracteristics					
Q _r	recovered charge	I _F = 10 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; <u>Fig. 8</u> ; <u>Fig. 9</u>	-	15	22	nC
C_d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	300	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	34	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	28	40	pF





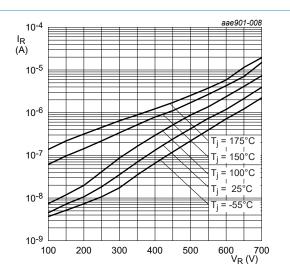
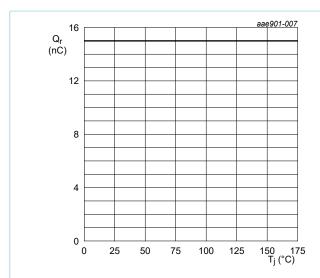


Fig. 7. Reverse current as a function of reverse voltage; typical values

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Silicon Carbide Diode





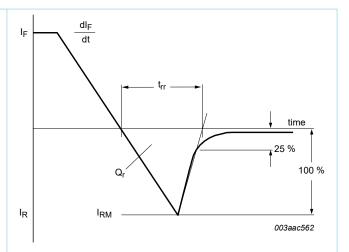
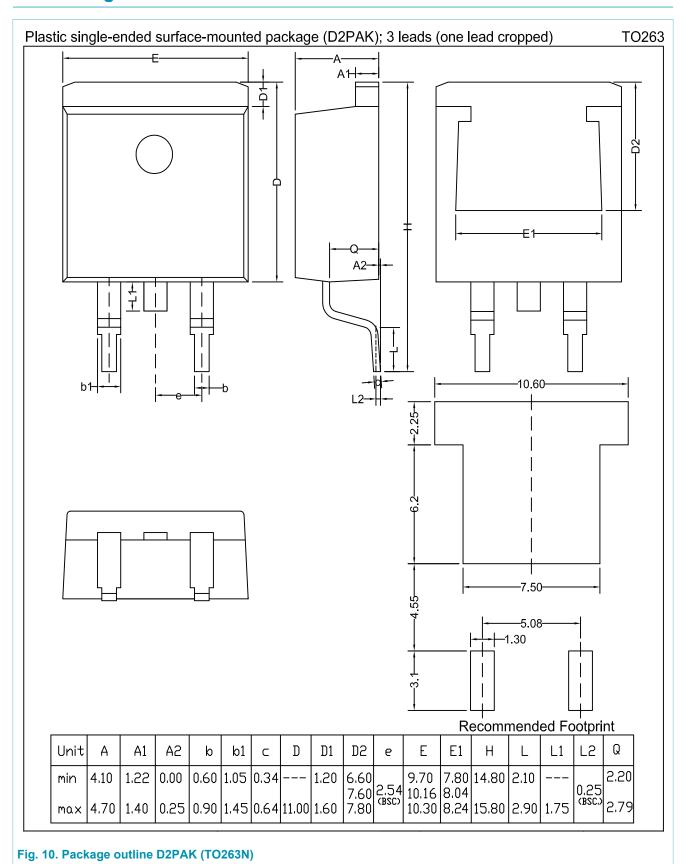


Fig. 9. Reverse recovery definitions; ramp recovery

10. Package outline



NXPSC10650B

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Document status [1][2]	Product status [3]	Definition
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